

IPD50P03P4L11ATMA1

IPD50P03P4L11ATMA1 Information



For Reference Only

Part Number IPD50P03P4L11ATMA1

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 30V 50A TO252-3 **Package** TO-252-3, DPak (2 Leads + Tab), SC-63

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IPD50P03P4L11ATMA1 Specifications

Manufacturer Part Number IPD50P03P4L11ATMA1 Manufacturer Infineon Technologies Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series OptiMOS? FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 50A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 85μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3770pF @ 25V Vgs (Max) +5V, -16V FET Feature - Power Dissipation (Max) 58W (Tc) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63		
CategoryDiscrete Semiconductor ProductsFackageTo-252-3, DPak (2 Leads + Tab), SC-63SeriesOptiMOS?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 85μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3770pF @ 25VVgs (Max)+5V, -16VFET Feature-Power Dissipation (Max)58W (Tc)Rds On (Max) @ Id, Vgs10.5 mOhm @ 50A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Manufacturer Part Number	IPD50P03P4L11ATMA1
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SeriesOptiMOS?FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 85μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3770pF @ 25VVgs (Max)+5V, -16VFET Feature-Power Dissipation (Max)58W (Tc)Rds On (Max) @ Id, Vgs10.5 mOhm @ 50A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63		Transistors - FETs, MOSFETs - Single
FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 50A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 2V @ 85μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3770pF @ 25V Vgs (Max) +5V, -16V FET Feature - Power Dissipation (Max) 58W (Tc) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Package	TO-252-3, DPak (2 Leads + Tab), SC-63
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C50A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 85μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3770pF @ 25VVgs (Max)+5V, -16VFET Feature-Power Dissipation (Max)58W (Tc)Rds On (Max) @ Id, Vgs10.5 mOhm @ 50A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Series	OptiMOS?
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Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Cate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature Surplier Device Package PG-TO252-3 Package / Case 50A (Tc) 50A (T	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2V @ 85μAGate Charge (Qg) (Max) @ Vgs55nC @ 10VInput Capacitance (Ciss) (Max) @ Vds3770pF @ 25VVgs (Max)+5V, -16VFET Feature-Power Dissipation (Max)58W (Tc)Rds On (Max) @ Id, Vgs10.5 mOhm @ 50A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id 2V @ 85μA Gate Charge (Qg) (Max) @ Vgs 55nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 3770pF @ 25V Vgs (Max) +5V, -16V FET Feature - Power Dissipation (Max) 58W (Tc) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Current - Continuous Drain (Id) @ 25°C	50A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +5V, -16V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case 55nC @ 10V 3770pF @ 25V +5V, -16V -5V	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) +5V, -16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs(th) (Max) @ Id	2V @ 85μA
Vgs (Max) +5V, -16V FET Feature - Power Dissipation (Max) 58W (Tc) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Gate Charge (Qg) (Max) @ Vgs	55nC @ 10V
FET Feature - Power Dissipation (Max) 58W (Tc) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Input Capacitance (Ciss) (Max) @ Vds	3770pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.5 mOhm @ 50A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Vgs (Max)	+5V, -16V
Rds On (Max) @ Id, Vgs10.5 mOhm @ 50A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeSurface MountSupplier Device PackagePG-TO252-3Package / CaseTO-252-3, DPak (2 Leads + Tab), SC-63	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Power Dissipation (Max)	58W (Tc)
Mounting Type Surface Mount Supplier Device Package PG-TO252-3 Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Rds On (Max) @ Id, Vgs	10.5 mOhm @ 50A, 10V
Supplier Device Package PG-TO252-3 Package / Case PG-TO252-3, DPak (2 Leads + Tab), SC-63	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Mounting Type	Surface Mount
	Supplier Device Package	PG-TO252-3
Report errors?	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63
		Report errors?

IPD50P03P4L11ATMA1 Guarantees



Ouality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IPD50P03P4L11ATMA1 Payment Methods



















IPD50P03P4L11ATMA1 Shipping Methods













If you have any question about IPD50P03P4L11ATMA1, please do not hesitate to contact us!

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